



N-Channel NexFET™ Power MOSFET

Check for Samples: CSD16414Q5

FEATURES

- Ultra Low Qg and Qgd
- Low Thermal Resistance
- Avalanche Rated
- · Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5mm × 6mm Plastic Package

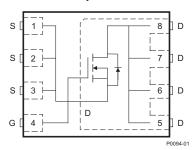
APPLICATIONS

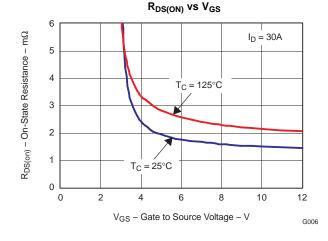
- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- Optimized for Synchronous FET Applications

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.

Top View





PRODUCT SUMMARY

V _{DS}	Drain to Source Voltage 25			V
Q_g	Gate Charge Total (4.5V) 16.6			nC
Q_{gd}	Gate Charge Gate to Drain	4.4		nC
Б	Design to Course On Besisters	V _{GS} = 4.5V 2.1		mΩ
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 10V 1.5		mΩ
V _{GS(th)}	Threshold Voltage	1.6		V

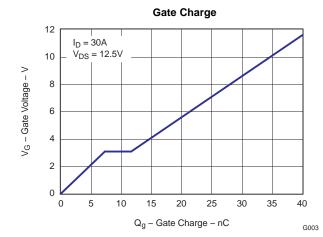
ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD16414Q5	SON 5 x 6 Plastic Package	13-inch reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	25	٧
V_{GS}	Gate to Source Voltage	+16 / -12	٧
	Continuous Drain Current, T _C = 25°C	100	Α
I _D	Continuous Drain Current ⁽¹⁾	34	Α
I _{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	213	Α
P_D	Power Dissipation ⁽¹⁾	3.2	W
T_J , T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	ů
E _{AS}	Avalanche Energy, single pulse $I_D = 100A$, $L = 0.1mH$, $R_G = 25\Omega$	500	mJ

- (1) $R_{\theta JA} = 39^{\circ}C/W$ on $1in^2$ Cu (2 oz.) on 0.060" thick FR4 PCB.
- (2) Pulse width ≤300μs, duty cycle ≤2%"



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ELECTRICAL CHARACTERISTICS

 $(T_{\Delta} = 25^{\circ}C \text{ unless otherwise stated})$

$(1_A = 25)$	°C unless otherwise stated)				
	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Static C	haracteristics				
BV_{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25		V
I_{DSS}	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 20V$		1	μΑ
I_{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +16/-12V$		100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.3 1.6	2	V
D	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 30A$	2.1	2.6	$m\Omega$
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 10V, I_D = 30A$	1.5	1.9	$m\Omega$
g _{fs} Transconductance		$V_{DS} = 15V, I_D = 30A$	138	1	S
Dynamic	Characteristics				
C _{ISS}	Input Capacitance		2810	3650	рF
C _{OSS}	Output Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V, f = 1MHz$	2040	2650	рF
C _{RSS}	Reverse Transfer Capacitance		140	180	pF
R_g	Series Gate Resistance		1.4	2.8	Ω
Qg	Gate Charge Total (4.5V)		16.6	21	nC
Q _{gd}	Gate Charge Gate to Drain	V 42.5V ID 20A	4.4		nC
Q _{gs}	Gate Charge Gate to Source	V _{DS} = 12.5V, ID = 30A	7.3		nC
Qg(th)	Gate Charge at Vth		4.5		nC
Q _{OSS}	Output Charge	V _{DS} = 13.5V, VGS = 0V	40	1	nC
t _{d(on)}	Turn On Delay Time		15		ns
t _r	Rise Time	V _{DS} = 12.5V, V _{GS} = 4.5V, I _D = 30A	24		ns
t _{d(off)}	Turn Off Delay Time	$R_G = 2\Omega$	18.4		ns
t _f	Fall Time		11.1		ns
Diode C	haracteristics				
V _{SD}	Diode Forward Voltage	I _S = 30A, V _{GS} = 0V	0.81	1	V
Q _{rr}	Reverse Recovery Charge	$V_{dd} = 13.5V$, $I_F = 30A$, $di/dt = 300A/\mu s$	44		nC
t _{rr}	Reverse Recovery Time	$V_{dd} = 13.5V$, $I_F = 30A$, $di/dt = 300A/\mu s$	35		ns

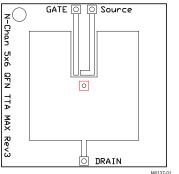
THERMAL CHARACTERISTICS

	PARAMETER	MIN	TYP	MAX	UNIT
R ₀ JC	Thermal Resistance Junction to Case (1)			1.1	°C/W
R _{θJA}	Thermal Resistance Junction to Ambient ⁽¹⁾ (2)			50	°C/W

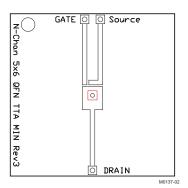
⁽¹⁾ R $_{\theta JC}$ is determined with the device mounted on a 1 inch square 2 oz. Cu pad on a 1.5 x 1.5 in 0.060 inch thick FR4 board. R $_{\theta JC}$ is specified by design while R $_{\theta JA}$ is determined by the user's board design.

⁽²⁾ Device mounted on FR4 Material with 1 inch² of 2 oz. Cu.





Max $R_{\theta JA} = 50$ °C/W when mounted on 1inch² of 2 oz. Cu.



Max $R_{\theta JA} = 122^{\circ}C/W$ when mounted on minimum pad area of 2 oz. Cu.

TYPICAL MOSFET CHARACTERISTICS

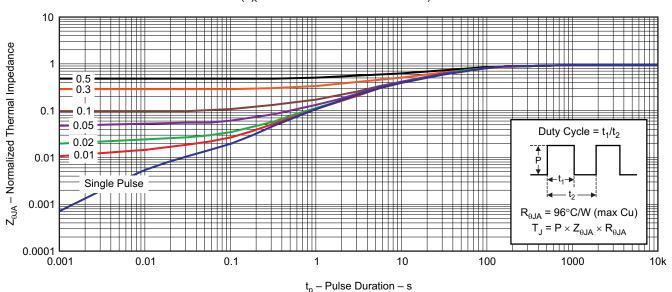


Figure 1. Transient Thermal Impedance



TYPICAL MOSFET CHARACTERISTICS (continued)

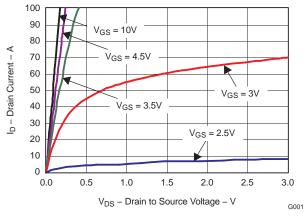


Figure 2. Saturation Characteristics

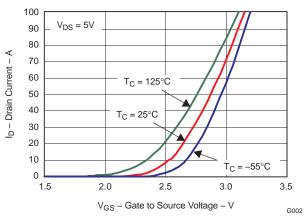


Figure 3. Transfer Characteristics

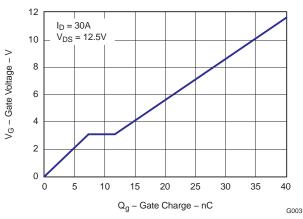


Figure 4. Gate Charge

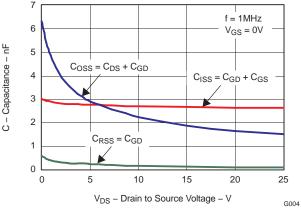


Figure 5. Capacitance

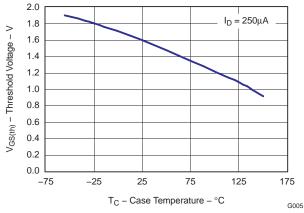


Figure 6. Threshold Voltage vs. Temperature

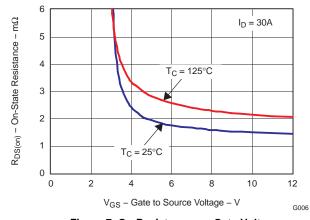


Figure 7. On Resistance vs. Gate Voltage



TYPICAL MOSFET CHARACTERISTICS (continued)

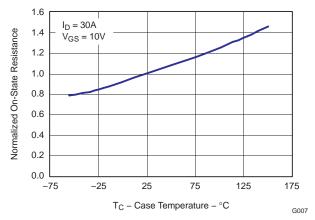


Figure 8. On Resistance vs. Temperature

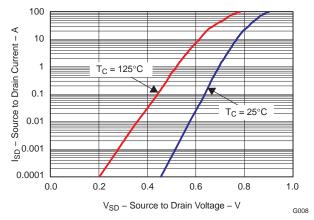


Figure 9. Typical Diode Forward Voltage

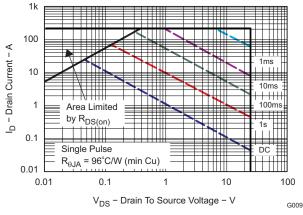


Figure 10. Maximum Safe Operating Area

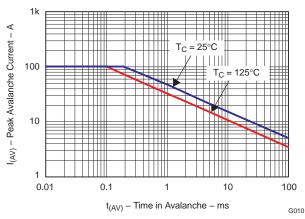


Figure 11. Single Pulse Unclamped Inductive Switching

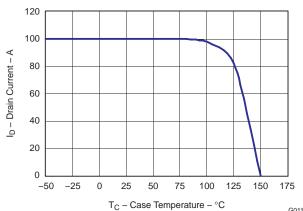
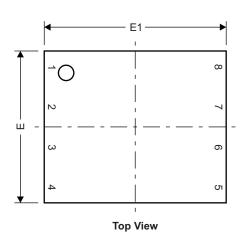


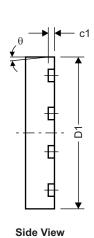
Figure 12. Maximum Drain Current vs. Temperature

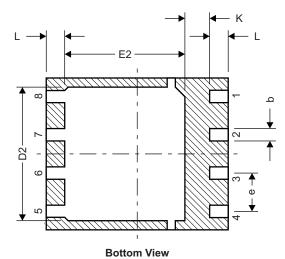


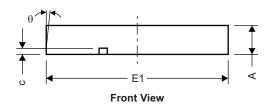
MECHANICAL DATA

Q5 Package Dimensions









M0140-01

DIM	MILLIM	ETERS	INCI	HES
DIW	MIN	MAX	MIN	MAX
Α	0.950	1.050	0.037	0.039
b	0.360	0.460	0.014	0.018
С	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
D1	4.900	5.100	0.193	0.201
D2	4.320	4.520	0.170	0.178
Е	4.900	5.100	0.193	0.201
E1	5.900	6.100	0.232	0.240
E2	3.920	4.12	0.154	0.162
е	1.27	TYP	0.0	50
K	0.760		0.030	
L	0.510	0.710	0.020	0.028
θ	0.00			

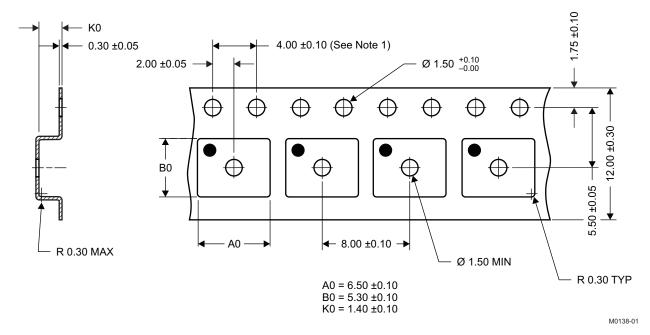


Recommended PCB Pattern								
F6 — F1 —	F7							
F10	4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4							

DIM	MILLIM	ETERS	INCHES		
DIN	MIN	MAX	MIN	MAX	
F1	6.205	6.305	0.244	0.248	
F2	4.460	4.560	0.176	0.180	
F3	4.460	4.560	0.176	0.180	
F4	0.650	0.700	0.026	0.028	
F5	0.620	0.670	0.024	0.026	
F6	0.630	0.680	0.025	0.027	
F7	0.700	0.800	0.028	0.031	
F8	0.650	0.700	0.026	0.028	
F9	0.620	0.670	0.024	0.026	
F10	4.900	5.000	0.193	0.197	
F11	4.460	4.560	0.176	0.180	

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q5 Tape and Reel Information



Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. Thickness: 0.30 ±0.05mm
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible



REVISION HISTORY

Cł	changes from Original (August 2009) to Revision A	Page
•	Deleted the Package Marking Information section	

11-Nov-2025

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PACKAGING INFORMATION

Ī	Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
L							(4)	(5)		
	CSD16414Q5	Active	Production	VSON-CLIP (DQH) 8	2500 LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD16414
	CSD16414Q5.B	Active	Production	VSON-CLIP (DQH) 8	2500 LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD16414

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

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